Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	75
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 20x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21388cnfp-u0

1.1.2 Specifications

Tables 1.1 and 1.2 outline the Specifications for R8C/38C Group.

Table 1.1 Specifications for R8C/38C Group (1)

Item	Function	Specification
CPU	Central processing unit	R8C CPU core • Number of fundamental instructions: 89 • Minimum instruction execution time: 50 ns (f(XIN) = 20 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 1.8 to 5.5 V) • Multiplier: 16 bits × 16 bits → 32 bits • Multiply-accumulate instruction: 16 bits × 16 bits + 32 bits → 32 bits • Operation mode: Single-chip mode (address space: 1 Mbyte)
Memory	ROM, RAM, Data flash	Refer to **Table 1.3 Product List for R8C/38C Group**
Power Supply Voltage Detection	Voltage detection circuit	• Power-on reset • Voltage detection 3 (detection level of voltage detection 0 and voltage detection 1 selectable)
I/O Ports	Programmable I/O ports	• Input-only: 1 pin • CMOS I/O ports: 75, selectable pull-up resistor • High current drive ports: 75
Clock	Clock generation circuits	• 4 circuits: XIN clock oscillation circuit, XCIN clock oscillation circuit (32 kHz), High-speed on-chip oscillator (with frequency adjustment function), Low-speed on-chip oscillator • Oscillation stop detection: XIN clock oscillation stop detection function • Frequency divider circuit: Dividing selectable 1, 2, 4, 8, and 16 • Low power consumption modes: Standard operating mode (high-speed clock, low-speed clock, high-speed on-chip oscillator, low-speed on-chip oscillator), wait mode, stop mode
		Real-time clock (timer RE)
Interrupts		• Interrupt Vectors: 69 • External: 9 sources ($\overline{\text{INT}}$ × 5, key input × 4) • Priority levels: 7 levels
Watchdog Timer		• 14 bits × 1 (with prescaler) • Reset start selectable • Low-speed on-chip oscillator for watchdog timer selectable
DTC (Data Transfer Controller)		• 1 channel • Activation sources: 39 • Transfer modes: 2 (normal mode, repeat mode)
Timer	Timer RA	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), pulse output mode (output level inverted every period), event counter mode, pulse width measurement mode, pulse period measurement mode
	Timer RB	8 bits × 1 (with 8-bit prescaler) Timer mode (period timer), programmable waveform generation mode (PWM output), programmable one-shot generation mode, programmable wait one-shot generation mode
	Timer RC	16 bits × 1 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 3 pins), PWM2 mode (PWM output pin)
	Timer RD	16 bits × 2 (with 4 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 6 pins), reset synchronous PWM mode (output three-phase waveforms (6 pins), sawtooth wave modulation), complementary PWM mode (output three-phase waveforms (6 pins), triangular wave modulation), PWM3 mode (PWM output 2 pins with fixed period)

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

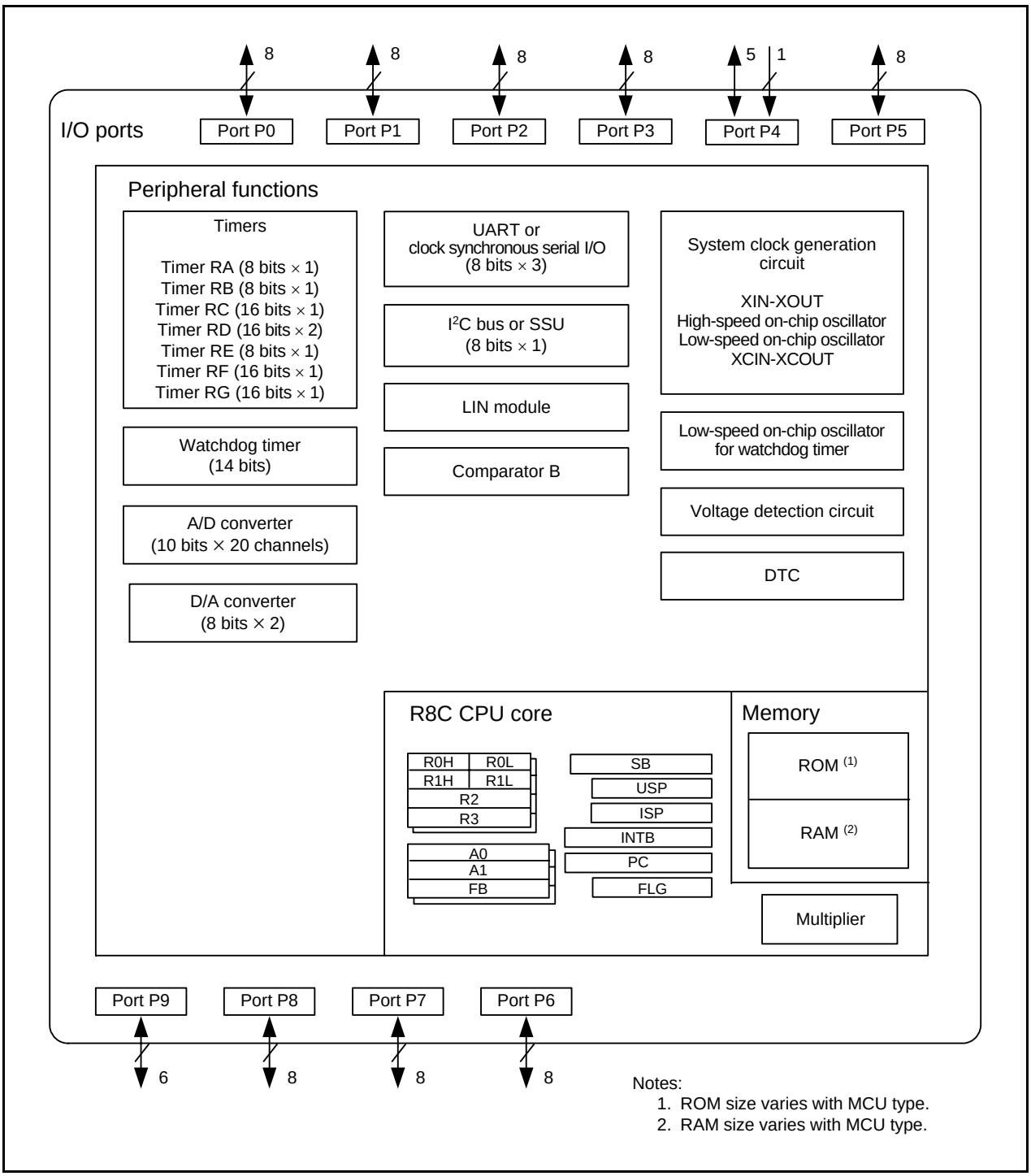
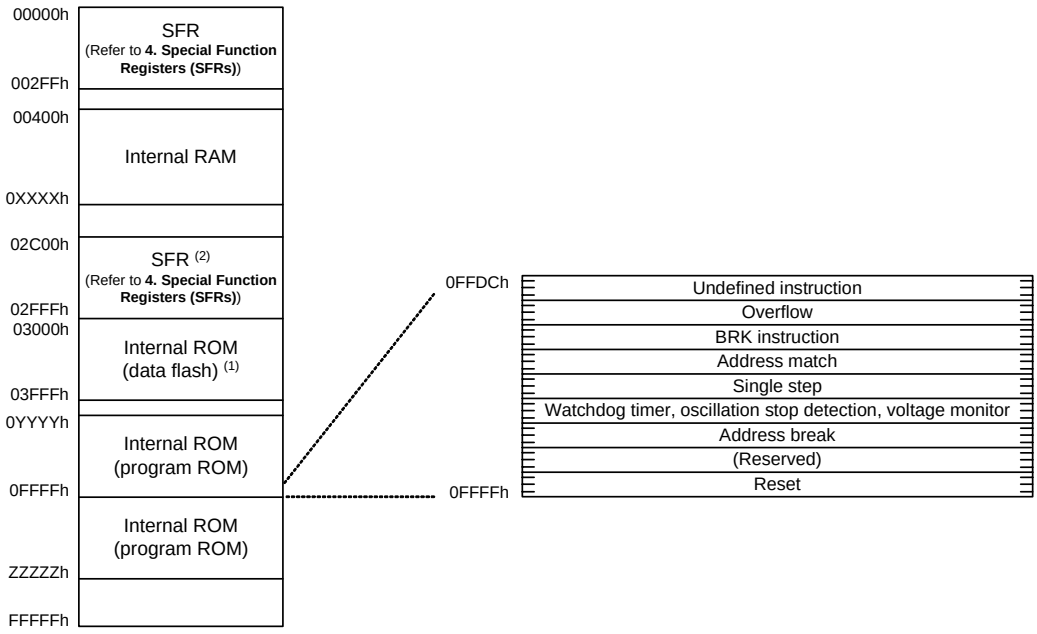


Figure 1.2 Block Diagram

3. Memory

3.1 R8C/38C Group

Figure 3.1 is a Memory Map of R8C/38C Group. The R8C/38C Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 64-Kbyte internal ROM area is allocated addresses 04000h to 13FFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 6-Kbyte internal RAM area is allocated addresses 00400h to 01BFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh (the SFR areas for the DTC and other modules). Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. The data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The SFR areas for the DTC and other modules are allocated to addresses 02C00h to 02FFFh.
3. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F21386CNFP, R5F21386CDFP, R5F21386CNXXXFP, R5F21386CDXXXFP	32 Kbytes	08000h	–	2.5 Kbytes	00DFFh
R5F21387CNFP, R5F21387CDFP, R5F21387CNXXXFP, R5F21387CDXXXFP	48 Kbytes	04000h	–	4 Kbytes	013FFh
R5F21388CNFP, R5F21388CDFP, R5F21388CNXXXFP, R5F21388CDXXXFP	64 Kbytes	04000h	13FFFh	6 Kbytes	01BFFh
R5F2138ACNFP, R5F2138ACDFP, R5F2138ACNXXXFP, R5F2138ACDXXXFP	96 Kbytes	04000h	1BFFFh	8 Kbytes	023FFh
R5F2138CCNFP, R5F2138CCDFP, R5F2138CCNXXXFP, R5F2138CCDXXXFP	128 Kbytes	04000h	23FFFh	10 Kbytes	02BFFh

Figure 3.1 Memory Map of R8C/38C Group

Table 4.2 SFR Information (2) (1)

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h			
0044h			
0045h			
0046h	INT4 Interrupt Control Register	INT4IC	XX00X000b
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h	Timer RD0 Interrupt Control Register	TRD0IC	XXXXX000b
0049h	Timer RD1 Interrupt Control Register	TRD1IC	XXXXX000b
004Ah	Timer RE Interrupt Control Register	TREIC	XXXXX000b
004Bh	UART2 Transmit Interrupt Control Register	S2TIC	XXXXX000b
004Ch	UART2 Receive Interrupt Control Register	S2RIC	XXXXX000b
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register/IIC bus Interrupt Control Register (2)	SSUIC/IICIC	XXXXX000b
0050h	Timer RF Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h	UART1 Transmit Interrupt Control Register	S1TIC	XXXXX000b
0054h	UART1 Receive Interrupt Control Register	S1RIC	XXXXX000b
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RA Interrupt Control Register	TRAIC	XXXXX000b
0057h			
0058h	Timer RB Interrupt Control Register	TRBIC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh	Timer RF Interrupt Control Register	TRFIC	XXXXX000b
005Ch	Timer RF Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh	UART2 Bus Collision Detection Interrupt Control Register	U2BCNIC	XXXXX000b
005Fh	Timer RF Capture Interrupt Control Register	CAPIC	XXXXX000b
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh	Timer RG Interrupt Control Register	TRGIC	XXXXX000b
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage Monitor 1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage Monitor 2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.8 SFR Information (8) (1)

Address	Register	Symbol	After Reset
01C0h	Address Match Interrupt Register 0	RMAD0	XXh
01C1h			XXh
01C2h			0000XXXXb
01C3h	Address Match Interrupt Enable Register 0	AIER0	00h
01C4h	Address Match Interrupt Register 1	RMAD1	XXh
01C5h			XXh
01C6h			0000XXXXb
01C7h	Address Match Interrupt Enable Register 1	AIER1	00h
01C8h			
01C9h			
01CAh			
01CBh			
01CCh			
01CDh			
01CEh			
01CFh			
01D0h			
01D1h			
01D2h			
01D3h			
01D4h			
01D5h			
01D6h			
01D7h			
01D8h			
01D9h			
01DAh			
01DBh			
01DCh			
01DDh			
01DEh			
01DFh			
01E0h	Pull-Up Control Register 0	PUR0	00h
01E1h	Pull-Up Control Register 1	PUR1	00h
01E2h	Pull-Up Control Register 2	PUR2	00h
01E3h			
01E4h			
01E5h			
01E6h			
01E7h			
01E8h			
01E9h			
01EAh			
01EBh			
01ECh			
01EDh			
01EEh			
01EFh			
01F0h	Port P1 Drive Capacity Control Register	P1DRR	00h
01F1h	Port P2 Drive Capacity Control Register	P2DRR	00h
01F2h	Drive Capacity Control Register 0	DRR0	00h
01F3h	Drive Capacity Control Register 1	DRR1	00h
01F4h	Drive Capacity Control Register 2	DRR2	00h
01F5h	Input Threshold Control Register 0	VLT0	00h
01F6h	Input Threshold Control Register 1	VLT1	00h
01F7h	Input Threshold Control Register 2	VLT2	00h
01F8h	Comparator B Control Register 0	INTCMP	00h
01F9h			
01FAh	External Input Enable Register 0	INTEN	00h
01FBh	External Input Enable Register 1	INTEN1	00h
01FCh	INT Input Filter Select Register 0	INTF	00h
01FDh	INT Input Filter Select Register 1	INTF1	00h
01FEh	Key Input Enable Register 0	KIEN	00h
01FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 5.2 Recommended Operating Conditions (1)

Symbol	Parameter				Conditions	Standard			Unit
						Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage					1.8	—	5.5	V
V_{SS}/AV_{SS}	Supply voltage					—	0	—	V
V_{IH}	Input “H” voltage	Other than CMOS input				0.8 V_{CC}	—	V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.5 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.55 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.65 V_{CC}	—	V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.65 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.7 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.8 V_{CC}	—	V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0.85 V_{CC}	—	V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0.85 V_{CC}	—	V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0.85 V_{CC}	—	V_{CC}	V
		External clock input (XOUT)				1.2	—	V_{CC}	V
V_{IL}	Input “L” voltage	Other than CMOS input				0	—	0.2 V_{CC}	V
		CMOS input	Input level switching function (I/O port)	Input level selection: 0.35 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.2 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.2 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.5 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.4 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.3 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.2 V_{CC}	V
				Input level selection: 0.7 V_{CC}	4.0 V ≤ V_{CC} ≤ 5.5 V	0	—	0.55 V_{CC}	V
					2.7 V ≤ V_{CC} < 4.0 V	0	—	0.45 V_{CC}	V
					1.8 V ≤ V_{CC} < 2.7 V	0	—	0.35 V_{CC}	V
		External clock input (XOUT)				0	—	0.4	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$				—	—	–160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$				—	—	–80	mA
$I_{OH(peak)}$	Peak output “H” current	Drive capacity Low				—	—	–10	mA
		Drive capacity High				—	—	–40	mA
$I_{OH(avg)}$	Average output “H” current	Drive capacity Low				—	—	–5	mA
		Drive capacity High				—	—	–20	mA
$I_{OL(sum)}$	Peak sum output “L” current	Sum of all pins $I_{OL(peak)}$				—	—	160	mA
$I_{OL(sum)}$	Average sum output “L” current	Sum of all pins $I_{OL(avg)}$				—	—	80	mA
$I_{OL(peak)}$	Peak output “L” current	Drive capacity Low				—	—	10	mA
		Drive capacity High				—	—	40	mA
$I_{OL(avg)}$	Average output “L” current	Drive capacity Low				—	—	5	mA
		Drive capacity High				—	—	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$f_{(XCIN)}$	XCIN clock input oscillation frequency				1.8 V ≤ V_{CC} ≤ 5.5 V	—	32.768	50	kHz
fOCO40M	When used as the count source for timer RC, timer RD or timer RG (3)				2.7 V ≤ V_{CC} ≤ 5.5 V	32	—	40	MHz
fOCO-F	fOCO-F frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
—	System clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz
$f_{(BCLK)}$	CPU clock frequency				2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	20	MHz
					1.8 V ≤ V_{CC} < 2.7 V	—	—	5	MHz

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.
3. fOCO40M can be used as the count source for timer RC, timer RD, or timer RG in the range of V_{CC} = 2.7 to 5.5 V.

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
—	Resolution		V_{ref} = AV_{CC}		—	—	10	Bit
—	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
ϕAD	A/D conversion clock		4.0 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	20	MHz
			3.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	16	MHz
			2.7 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	10	MHz
			2.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	5	MHz
—	Tolerance level impedance				—	3	—	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	—	—	µs
I_{Vref}	V_{ref} current		V_{CC} = 5.0 V, XIN = f1 = ϕAD = 20 MHz		—	45	—	µA
V_{ref}	Reference voltage				2.2	—	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	—	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		10,000 (3)	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1500	µs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1500	µs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20 (7)	—	85	°C
—	Data hold time (8)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40 °C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

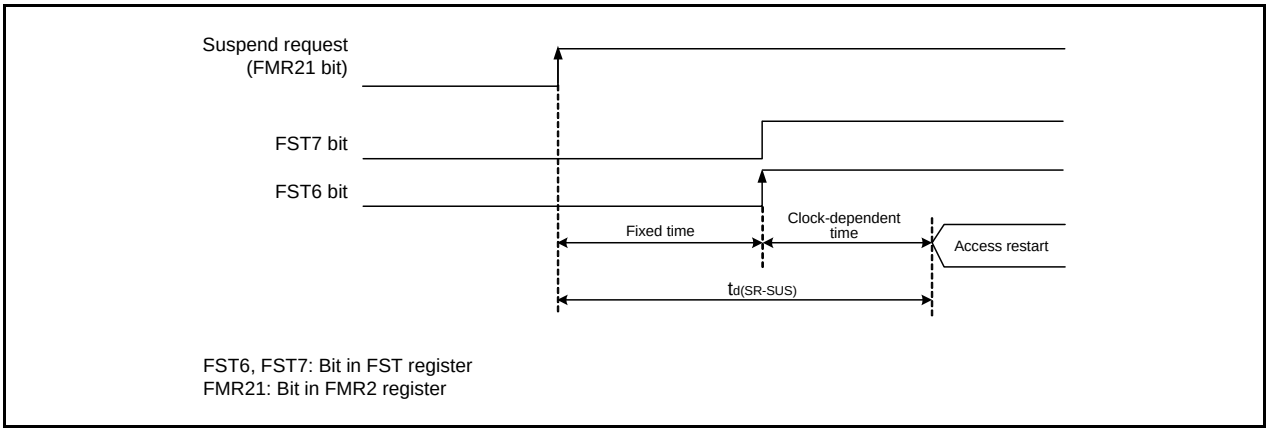


Figure 5.2 Time delay until Suspend

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time (4)	At the falling of V_{CC} from 5.0 V to (Vdet0_0 – 0.1) V	—	6	150	µs
—	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	—	1.5	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of V_{CC}	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of V_{CC}	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of V_{CC}	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of V_{CC}	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of V_{CC}	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of V_{CC}	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of V_{CC}	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of V_{CC}	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of V_{CC}	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of V_{CC}	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of V_{CC}	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of V_{CC}	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of V_{CC}	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of V_{CC}	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of V_{CC}	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of V_{CC}	4.20	4.45	4.75	V
—	Hysteresis width at the rising of V_{CC} in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	—	0.07	—	V
		Vdet1_6 to Vdet1_F selected	—	0.10	—	V
—	Voltage detection 1 circuit response time (3)	At the falling of V_{CC} from 5.0 V to (Vdet1_0 – 0.1) V	—	60	150	µs
—	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	—	1.7	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	38.4	40	41.6	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	35.389	36.864	38.338	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	30.72	32	33.28	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	30.40	32	33.60	MHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	0.5	3	ms
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	400	—	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/−40 to 85 °C (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	30	100	µs
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	2	—	µA

Note:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/−40 to 85 °C (D version), unless otherwise specified.

Table 5.14 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on (2)		—	—	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25 °C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.15 Timing Requirements of Synchronous Serial Communication Unit (SSU)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	—	—	t_{CYC} (2)
t_{HI}	SSCK clock “H” width			0.4	—	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	—	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		—	—	1	t_{CYC} (2)
		Slave		—	—	1	µs
t_{FALL}	SSCK clock falling time	Master		—	—	1	t_{CYC} (2)
		Slave		—	—	1	µs
t_{SU}	SSO, SSI data input setup time			100	—	—	ns
t_H	SSO, SSI data input hold time			1	—	—	t_{CYC} (2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC}$ + 50	—	—	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC}$ + 50	—	—	ns
t_{OD}	SSO, SSI data output delay time			—	—	1	t_{CYC} (2)
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	—	—	$1.5t_{CYC}$ + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	—	—	$1.5t_{CYC}$ + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	—	—	$1.5t_{CYC}$ + 200	ns

Notes:
1. V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

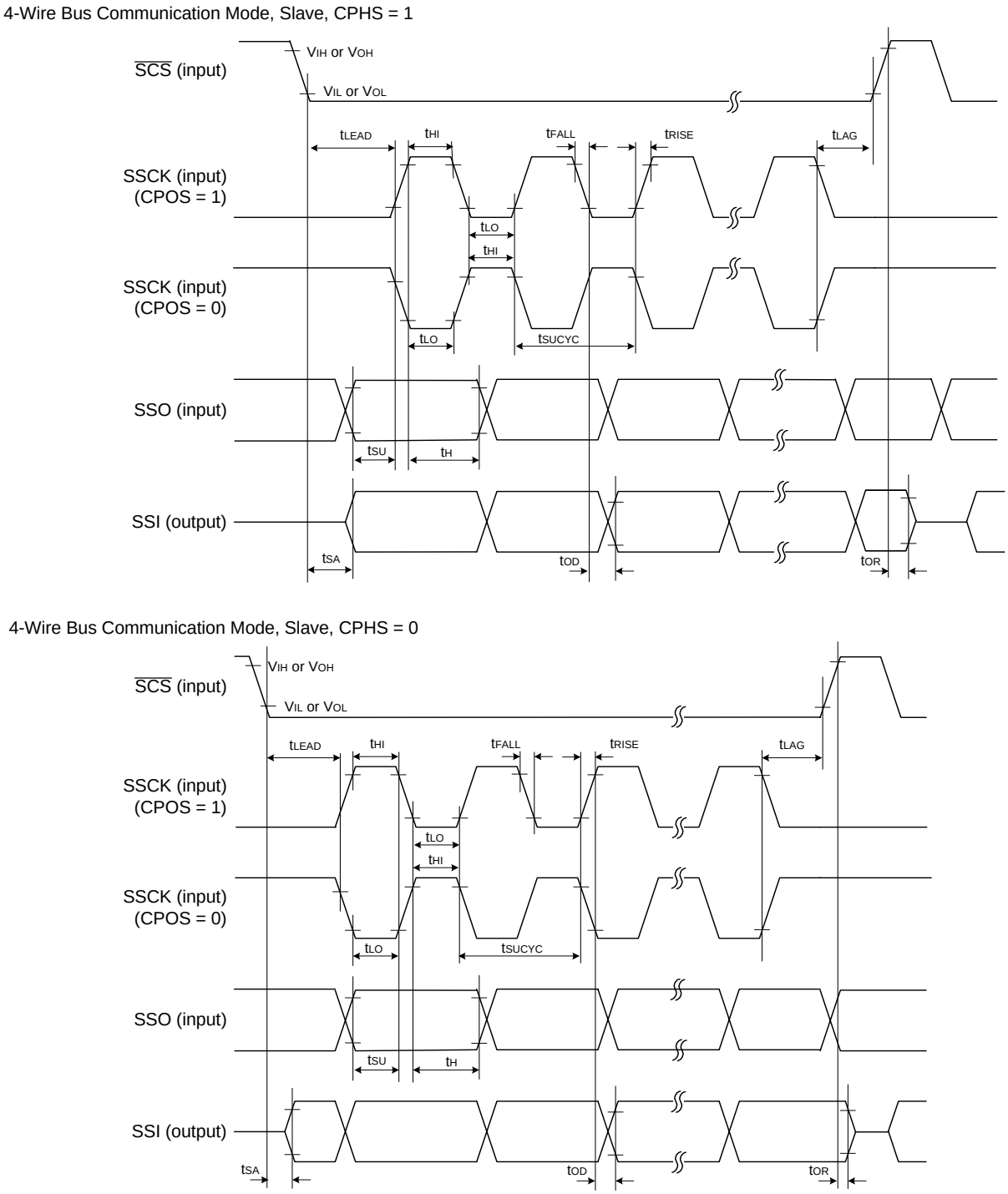


Figure 5.5 I/O Timing of Synchronous Serial Communication Unit (SSU) (Slave)

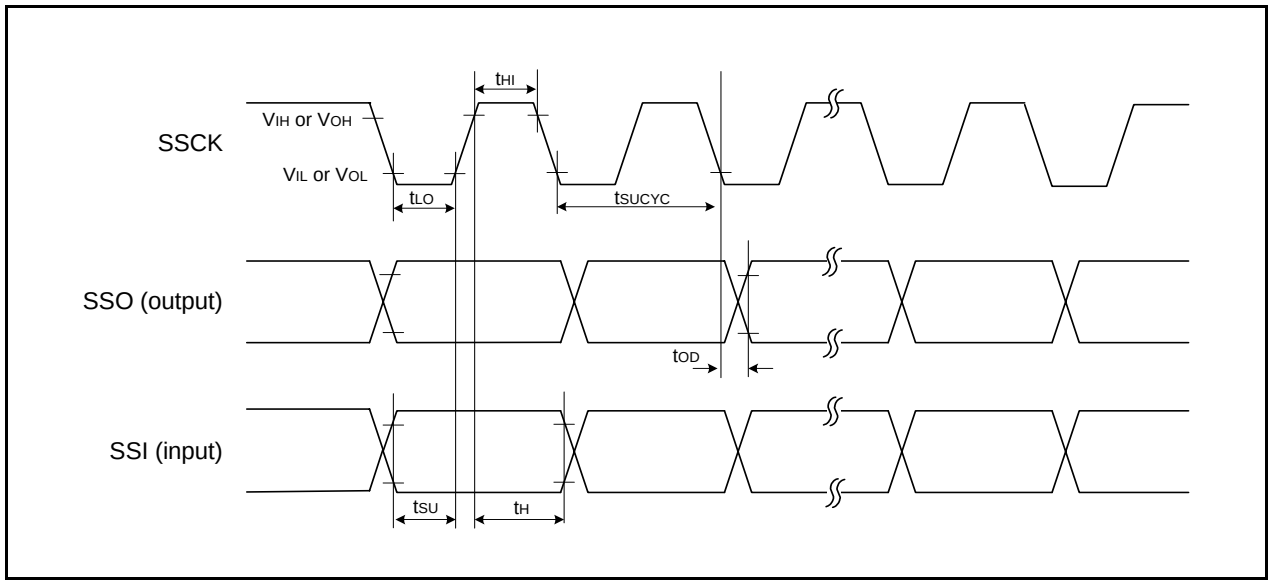


Figure 5.6 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

Table 5.18 Electrical Characteristics (2) [3.3 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	6.5	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	5.3	12.5	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.6	—	mA
			XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	2.2	—	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRD = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	400	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	—	85	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	—	47	—	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	100	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5.0	µA
			XIN clock off, Topr = 85 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	15	—	µA

Table 5.24 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	V_{CC} – 0.5	—	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	—	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	—	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, TRFI, $\overline{TRGIOA}$, TRGIOB, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 3.0 V		0.1	0.4	—	V
		$\overline{RESET}$	V_{CC} = 3.0 V		0.1	0.5	—	V
I_{IH}	Input “H” current		V_I = 3 V, V_{CC} = 3.0 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, V_{CC} = 3.0 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R_{fXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 2.7 V ≤ V_{CC} < 4.2 V, T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), and f(XIN) = 10 MHz, unless otherwise specified.

Table 5.25 Electrical Characteristics (4) [2.7 V ≤ Vcc ≤ 3.3 V]
(Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.5	10	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	7.5	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	4.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRD = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	390	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	—	80	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	—	40	—	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5.0	µA
			XIN clock off, Topr = 85 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	15	—	µA

Timing requirements (Unless Otherwise Specified: V_{CC} = 3 V, V_{SS} = 0 V, T_{opr} = 25 °C)

Table 5.26 External Clock Input (XOUT, XCIN)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	50	—	ns
$t_{WH(XOUT)}$	XOUT input “H” width	24	—	ns
$t_{WL(XOUT)}$	XOUT input “L” width	24	—	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	—	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	—	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	—	µs

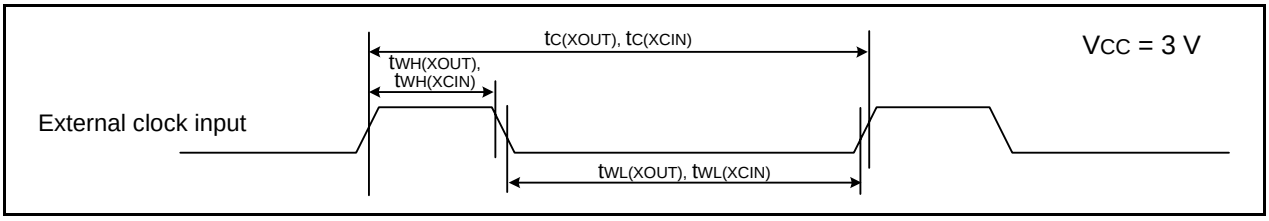


Figure 5.13 External Clock Input Timing Diagram when V_{CC} = 3 V

Table 5.27 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	300	—	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	120	—	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	120	—	ns

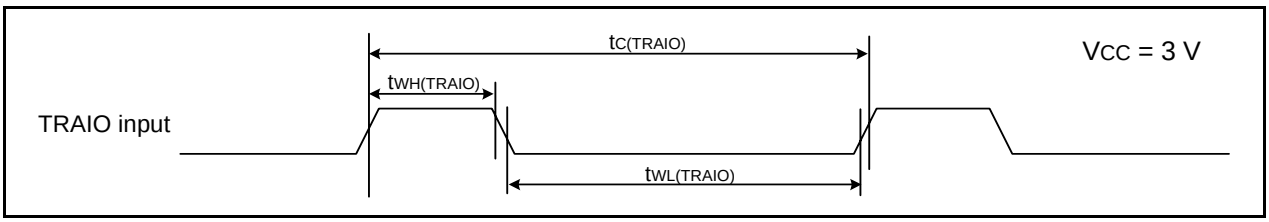


Figure 5.14 TRAIO Input Timing Diagram when V_{CC} = 3 V

Table 5.28 TRFI Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRFI)}$	TRFI input cycle time	1200 (1)	—	ns
$t_{WH(TRFI)}$	TRFI input “H” width	600 (2)	—	ns
$t_{WL(TRFI)}$	TRFI input “L” width	600 (2)	—	ns

Notes:
1. When using timer RF input capture mode, adjust the cycle time to (1/timer RF count source frequency × 3) or above.
2. When using timer RF input capture mode, adjust the pulse width to (1/timer RF count source frequency × 1.5) or above.

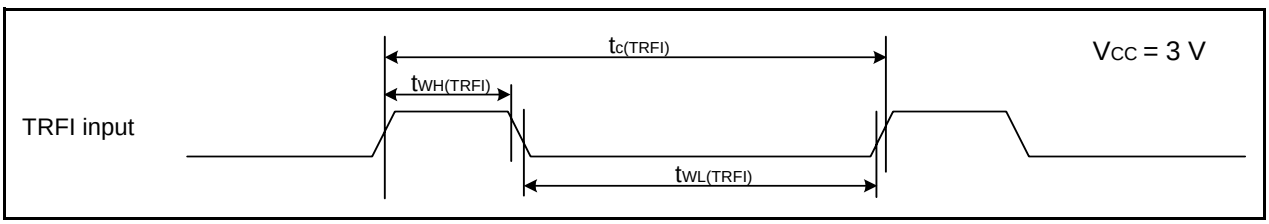


Figure 5.15 TRFI Input Timing Diagram when V_{CC} = 3 V

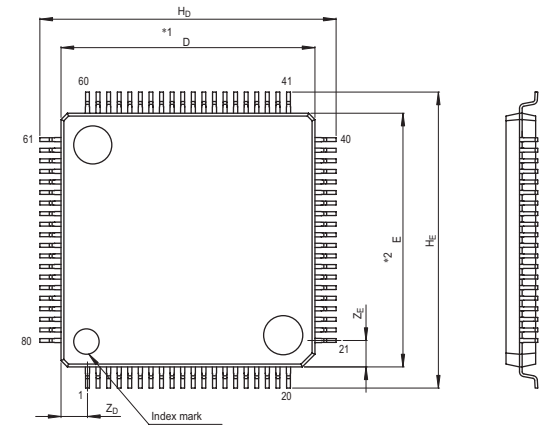
Table 5.32 Electrical Characteristics (6) [1.8 V ≤ Vcc < 2.7 V]
(Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.)

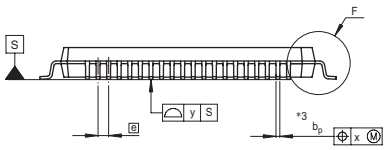
Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 1.8 to 2.7 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	2.2	—	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	0.8	—	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	2.5	10	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.7	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRD = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	—	80	350	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	—	40	—	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5	µA
			XIN clock off, Topr = 85 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	15	—	µA

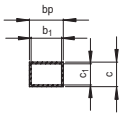
Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Electronics website.

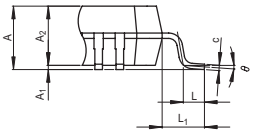
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP80-12x12-0.50	PLQP0080KB-A	80P6Q-A	0.5g







Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	11.9	12.0	12.1
E	11.9	12.0	12.1
A_2	—	1.4	—
H_D	13.8	14.0	14.2
H_E	13.8	14.0	14.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	10°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.25	—
Z_E	—	1.25	—
L	0.3	0.5	0.7
L_1	—	1.0	—

REVISION HISTORY	R8C/38C Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.01	Oct 30, 2009	—	First Edition issued
1.00	Apr 23, 2010	All pages	“Preliminary”, “Under development” deleted
		4	Table 1.3 revised
		27 to 53	“5. Electrical Characteristics” added
1.10	Nov 02, 2010	—	TN-R8C-A015A/E reflected
		3	Table 1.2 “Timer RG” revised
		4	Table 1.3 revised
		5	Figure 1.1 revised
		15	Figure 3.1 revised
		31	Table 5.3 “tCONV”, “tSAMP” revised
		45	Table 5.21 revised
		49	Table 5.28 revised
		53	Table 5.35 revised